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BCM® Bus Converter BCM6123xD1E13A3yzz



Isolated Fixed-Ratio DC-DC Converter

Features & Benefits

- Up to 125A continuous secondary current
- Up to 2208W/in³ power density
- 97.4% peak efficiency
- 4,242V_{DC} isolation
- Parallel operation for multi-kW arrays
- OV, OC, UV, short circuit and thermal protection
- BCM6123 through-hole ChiP package
 - 2.402 x 0.990 x 0.284in [61.00 x 25.14 x 7.21mm]
- PMBus™ management interface [a]

Typical Applications

- 380V_{DC} Power Distribution
- High-End Computing Systems
- Automated Test Equipment
- Industrial Systems
- High-Density Power Supplies
- Communications Systems
- Transportation

Product Ratings					
V _{PRI} = 384V (260 – 410V)	I_{SEC} = up to 125A				
V _{SEC} = 12V (8.1 – 12.8V) (NO LOAD)	K = 1/32				

Product Description

The BCM6123xD1E13A3yzz is a high-efficiency Bus Converter, operating from a 260 to 410V $_{\rm DC}$ primary bus to deliver an isolated, ratiometric secondary voltage from 8.1 to 12.8V $_{\rm DC}$.

The BCM6123xD1E13A3yzz offers low noise, fast transient response, and industry leading efficiency and power density. In addition, it provides an AC impedance beyond the bandwidth of most downstream regulators, allowing input capacitance normally located at the input of a PoL regulator to be located at the primary side of the BCM. With a primary to secondary K factor of 1/32, that capacitance value can be reduced by a factor of 1024x, resulting in savings of board area, material and total system cost.

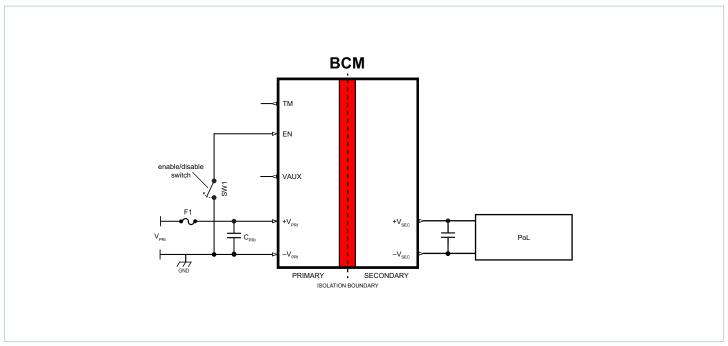
Leveraging the thermal and density benefits of Vicor ChiP packaging technology, the BCM offers flexible thermal management options with very low top and bottom side thermal impedances. Thermally-adept ChiP-based power components enable customers to achieve low cost power system solutions with previously unattainable system size, weight and efficiency attributes quickly and predictably.

This product can operate in the reverse direction, at full rated current, after being previously started in the forward direction.

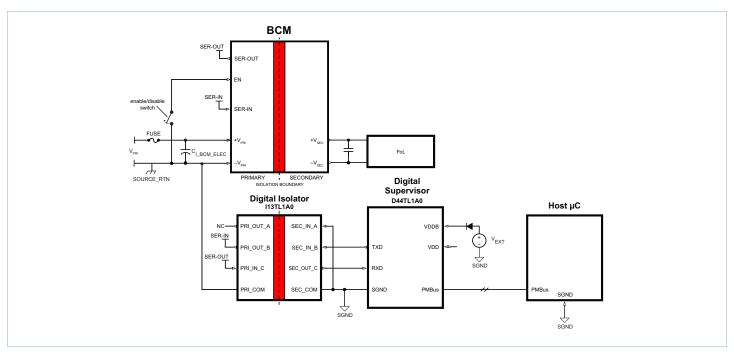


[[]a] When used with D44TL1A0 and I13TL1A0

Typical Applications

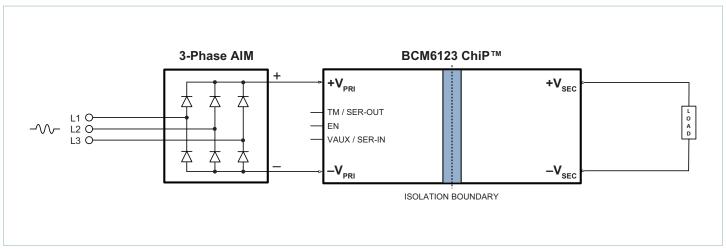


BCM6123xD1E13A3y00 at point-of-load



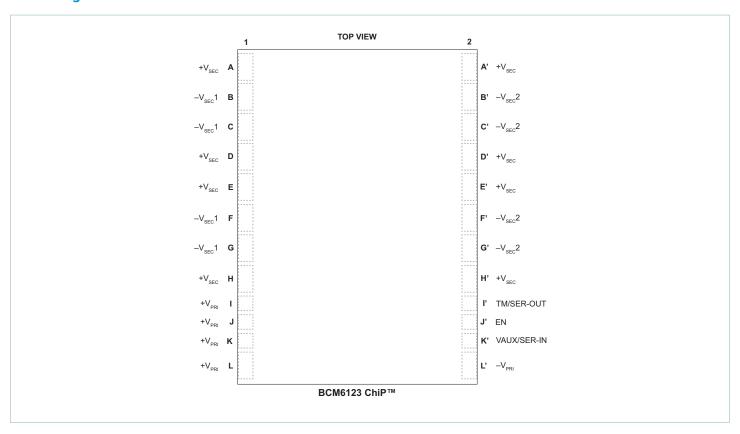
BCM6123xD1E13A3y01 at point-of-load

Typical Applications (Cont.)



3-phase AC to point-of-load (3-phase AIM TM + BCM6123xD1E13A3yzz)

Pin Configuration



Pin Descriptions

			Power Pins									
Pin Number	Signal Name	Туре	Function									
I1, J1, K1, L1	+V _{PRI}	PRIMARY POWER	Positive primary transformer power terminal									
L'2	–V _{PRI}	PRIMARY POWER RETURN	Negative primary transformer power terminal									
A1, D1, E1, H1, A'2, D'2, E'2, H'2	+V _{SEC}	SECONDARY POWER	Positive secondary transformer power terminal									
B1, C1, F1, G1 B'2, C'2, F'2, G'2												
		Analo	g Control Signal Pins									
Pin Number	Signal Name	Туре	Function									
ľ2	TM	OUTPUT	Temperature Monitor; primary side referenced signals									
J′2	EN	INPUT	Enables and disables power supply; primary side referenced signals									
K'2	VAUX	OUTPUT	Augilian Valtana Causas missan sida safaran and simala									
PMBus™ Control Signal Pins												
			Auxiliary Voltage Source; primary side referenced signals TM Control Signal Pins									
Pin Number	Signal Name											
Pin Number		PMBus	™ Control Signal Pins									
	Signal Name	PMBus Type	TM Control Signal Pins Function									

 $^{^{\}text{[b]}}$ For proper operation an external low impedance connection must be made between listed $-V_{SEC}1$ and $-V_{SEC}2$ terminals.



Part Ordering Information

Product Function	Package Size	Package Mounting	Max Primary Input Voltage	Range Identifier	Max Secondary Voltage	Secondary Output Current	Temperature Grade	Option
всм	6123	Х	D1	Е	13	А3	у	ZZ
Bus Converter Module	61 = L 23 = W	T = TH	410V	260 – 410V	13V No Load	125A	T = -40 to 125°C M = -55 to 125°C	 00 = Analog Ctrl 01 = PMBus Ctrl 0R = Reversible Analog Ctrl 0P = Reversible PMBus Ctrl

All products shipped in JEDEC standard high profile (0.400" thick) trays (JEDEC Publication 95, Design Guide 4.10).

Standard Models

Product Function	Package Size	Package Mounting	Max Primary Input Voltage	Range Identifier	Max Secondary Voltage	Secondary Output Current	Temperature Grade	Option
всм	6123	Т	D1	E	13	А3	Т	00
всм	6123	Т	D1	E	13	А3	Т	01
ВСМ	6123	Т	D1	E	13	А3	Т	OR
всм	6123	Т	D1	E	13	А3	Т	OP

Absolute Maximum Ratings

The absolute maximum ratings below are stress ratings only. Operation at or beyond these maximum ratings can cause permanent damage to the device.

Parameter	Comments	Min	Max	Unit
+V _{PRI_DC} to -V _{PRI_DC}		-1	480	V
V_{PRI_DC} or V_{SEC_DC} Slew Rate (Operational)			1	V/µs
+V _{SEC_DC} to -V _{SEC_DC}		-1	15	V
TM/SER-OUT to -V _{PRI_DC}			4.6	V
EN to -V _{PRI_DC}		-0.3	5.5	V
VAUX/SER-IN to -V _{PRI_DC}			4.6	V



Electrical Specifications

Attribute	Symbol	Conditions / Notes	Min	Тур	Max	Unit	
Ger	neral Powertra	in PRIMARY to SECONDARY Specification (Forward	Direction])			
Primary Input Voltage Range (Continuous)	V _{PRI_DC}		260		410	V	
V _{PRI} μController	$V_{\mu C_ACTIVE}$	V_{PRI_DC} voltage where μC is initialized, (i.e., VAUX = Low, powertrain inactive)			130	V	
PRI to SEC Input Quiescent Current	I _{PRI_Q}	Disabled, EN Low, $V_{PRI_DC} = 384V$ $T_{INTERNAL} \le 100^{\circ}C$		2	4	mA	
		$V_{PRI DC} = 384V$, $T_{INTERNAL} = 25^{\circ}C$		11	17		
DDI+- CEC N- I		V _{PRI_DC} = 384V	5.9	''	25	_	
PRI to SEC No-Load Power Dissipation	P _{PRI_NL}	V _{PRI_DC} = 260 - 410V, T _{INTERNAL} = 25°C	3.3		19	W	
		$V_{\text{PRI_DC}} = 260 - 410V$			27	-	
PRI to SEC Inrush Current Peak	I _{PRI INR PK}	$V_{PRI_DC} = 410V$, $C_{SEC_{EXT}} = 1000\mu F$, $R_{LOAD_{SEC}} = 50\%$ of full-load current		10		А	
The control of the co	'FRI_INK_FK	T _{INTERNAL} ≤ 100°C			15		
DC Primary Input Current	I _{PRI_IN_DC}	At I _{SEC_OUT_DC} = 125A, T _{INTERNAL} ≤ 100°C			4.1	А	
Transformation Ratio	K	Primary to secondary, $K = V_{SEC_DC} / V_{PRI_DC}$, at no load		1/32		V/V	
Secondary Output Current (Continuous)	I _{SEC_OUT_DC}				125	А	
Secondary Output Current (Pulsed)	I _{SEC_OUT_PULSE}	10ms pulse, 25% duty cycle, I _{SEC_OUT_AVG} ≤ 50% of rated I _{SEC_OUT_DC}			167	А	
Secondary Output Power (Continuous)	P _{SEC_OUT_DC}	Specified at V _{PRI_DC} = 410V			1500	W	
Secondary Output Power (Pulsed)	P _{SEC_OUT_PULSE}	Specified at V_{PRI_DC} = 410V; 10ms pulse, 25% duty cycle, $P_{SEC_AVG} \le 50\%$ of rated $P_{SEC_OUT_DC}$			2000	W	
		$V_{PRI_DC} = 384V$, $I_{SEC_OUT_DC} = 125A$	96.2	97			
PRI to SEC Efficiency (Ambient)	η_{AMB}	V _{PRI_DC} = 260 – 410V, I _{SEC_OUT_DC} = 125A	95.2			%	
	AWD	$V_{PRI_DC} = 384V$, $I_{SEC_OUT_DC} = 62.5A$	96.5	97.4			
PRI to SEC Efficiency (Hot)	η_{HOT}	$V_{PRI_DC} = 384V$, $I_{SEC_OUT_DC} = 125A$	95.8	97		%	
PRI to SEC Efficiency (Over Load Range)	η _{20%}	25A < I _{SEC_OUT_DC} < 125A	90			%	
	R _{SEC_COLD}	$V_{PRI_DC} = 384V$, $I_{SEC_OUT_DC} = 125A$, $T_{INTERNAL} = -40$ °C	1.10	1.50	1.80		
PRI to SEC Output Resistance	R _{SEC_AMB}	$V_{PRI_DC} = 384V$, $I_{SEC_OUT_DC} = 125A$	1.50	1.85	2.30	mΩ	
	R _{SEC_HOT}	$V_{PRI_DC} = 384V$, $I_{SEC_OUT_DC} = 125A$, $T_{INTERNAL} = 100$ °C	2.2	2.45	2.70		
Switching Frequency	F _{SW}	Frequency of the output voltage ripple = $2x F_{SW}$	0.95	1.00	1.05	MHz	
Secondary Output Voltage Ripple	V _{SEC_OUT_PP}	$C_{SEC_EXT} = 0\mu F$, $I_{SEC_OUT_DC} = 125A$, $V_{PRI_DC} = 384V$, 20MHz BW		195		mV	
		T _{INTERNAL} ≤ 100°C			250		
Primary Input Leads Inductance (Parasitic)	L _{PRI_IN_LEADS}	Frequency 2.5MHz (double switching frequency), simulated lead model		7		nH	
Secondary Output Leads Inductance (Parasitic)	L _{SEC_OUT_LEADS}	Frequency 2.5MHz (double switching frequency), simulated lead model		0.64		nH	
Primary Input Series Inductance (Internal)	L _{IN_INT}	Reduces the need for input decoupling inductance in BCM arrays		0.56		μΗ	



Attribute	Symbol	Conditions / Notes	Min	Тур	Max	Unit
Genera	al Powertrain I	PRIMARY to SECONDARY Specification (Forward Di	rection) Co	ont.		
Effective Primary Capacitance (Internal)	C _{PRI_INT}	Effective value at 384V _{PRL_DC}		0.37		μF
Effective Secondary Capacitance (Internal)	C _{SEC_INT}	Effective value at 12V _{SEC_DC}		208		μF
Rated Secondary Output Capacitance (External)	C _{SEC_OUT_EXT}	Excessive capacitance may drive module into short-circuit protection			1000	μF
Rated Secondary Output Capacitance (External), Parallel Array Operation	C _{SEC_OUT_AEXT}	$C_{SEC_OUT_AEXT}$ Max = N • 0.5 • $C_{SEC_OUT_EXT\ MAX}$, where N = the number of units in parallel				
	Powertrain I	Protection PRIMARY to SECONDARY (Forward Direction)	tion)			
Auto Restart Time	t _{AUTO_RESTART}	Start up into a persistent fault condition. Non-latching fault detection given $V_{PRI_DC} > V_{PRI_UVLO+}$	292.5		357.5	ms
Primary Overvoltage Lockout Threshold	V _{PRI_OVLO+}		420	434.5	450	V
Primary Overvoltage Recovery Threshold	V _{PRI_OVLO}		410	424	440	V
Primary Overvoltage Lockout Hysteresis	V _{PRI_OVLO_HYST}			10.5		V
Primary Overvoltage Lockout Response Time	t _{PRI_OVLO}			100		μs
Secondary Soft-Start Time	t _{SEC_SOFT-START}	From powertrain active; fast current limit protection disabled during soft start		1		ms
Secondary Output Overcurrent Trip Threshold	I _{SEC_OUT_OCP}		145	170	210	А
Secondary Output Overcurrent Response Time Constant	t _{SEC_OUT_OCP}	Effective internal RC filter		3		ms
Secondary Output Short-Circuit Protection Trip Threshold	I _{SEC_OUT_SCP}		187			А
Secondary Output Short-Circuit Protection Response Time	t _{SEC_OUT_SCP}			1		μs
Overtemperature Shut-Down Threshold	t _{OTP+}	Temperature sensor located inside controller IC	125			°C



Attribute	Symbol	Conditions / Notes	Min	Тур	Max	Unit
Po	owertrain Supe	ervisory Limits PRIMARY to SECONDARY (Forward I	Direction)			
Primary Overvoltage Lockout Threshold	V _{PRI_OVLO+}		420	434.5	450	V
Primary Overvoltage Recovery Threshold	V _{PRI_OVLO}		410	424	440	V
Primary Overvoltage Lockout Hysteresis	V _{PRI_OVLO_HYST}			10.5		V
Primary Overvoltage Lockout Response Time	t _{PRI_OVLO}			100		μs
Primary Undervoltage Lockout Threshold	V _{PRI_UVLO} _		195	221	250	V
Primary Undervoltage Recovery Threshold	V _{PRI_UVLO+}		225	243	255	V
Primary Undervoltage Lockout Hysteresis	V _{PRI_UVLO_HYST}			15		V
Primary Undervoltage Lockout Response Time	t _{PRI_UVLO}			100		μs
Primary-to-Secondary Start-Up Delay	t _{PRI_TO_SEC_DELAY}	From $V_{PRI_DC} = V_{PRI_UVLO_+}$ to powertrain active, EN floating (i.e., one-time start-up delay from application of V_{PRI_DC} to V_{SEC_DC})		20		ms
Secondary Output Overcurrent Trip Threshold	I _{SEC_OUT_OCP}		145	170	210	А
Secondary Output Overcurrent Response Time Constant	t _{SEC_OUT_OCP}	Effective internal RC filter		3		ms
Overtemperature Shut-Down Threshold	t _{OTP+}	Temperature sensor located inside controller IC	125			°C
Overtemperature Recovery Threshold	t _{OTP}		105	110	115	°C
Undertemperature Shut-Down Threshold	t _{UTP}	Temperature sensor located inside controller IC; Protection not available for M-Grade units.			- 45	°C
Undertemperature Restart Time	t _{UTP_RESTART}	Start up into a persistent fault condition. Non-latching fault detection given $V_{PRI_DC} > V_{PRI_UVLO+}$		3		S



Attribute	Symbol	Conditions / Notes	Min	Тур	Max	Unit	
Ger	neral Powertra	in SECONDARY to PRIMARY Specification (Reverse	e Direction))			
Secondary Input Voltage Range (Continuous)	V_{SEC_DC}		8.1		12.8	V	
		V _{SEC_DC} = 12V, T _{INTERNAL} = 25°C		11	17		
SEC to PRI No-Load	P _{SEC_NL}	$V_{SEC_DC} = 12V$	5.9		25	W	
Power Dissipation	' SEC_NL	V _{SEC_DC} = 8.1 – 12.8V, T _{INTERNAL} = 25°C			19	VV	
		$V_{SEC_DC} = 8.1 - 12.8V$			20		
DC Secondary Input Current	I _{SEC_IN_DC}	At I _{PRI_DC} = 3.9A, T _{INTERNAL} ≤ 100°C			127	А	
Primary Output Power (Continuous)	P _{PRI_OUT_DC}	Specified at $V_{SEC_DC} = 12.8V$			1500	W	
Primary Output Power (Pulsed)	P _{PRI_OUT_PULSE}	Specified at V_{SEC_DC} = 12.8V; 10ms pulse, 25% duty cycle, $P_{PRL_AVG} \le 50\%$ of rated $P_{PRL_OUT_DC}$			2000	W	
Primary Output Current (Continuous)	I _{PRI_OUT_DC}				3.9	А	
Primary Output Current (Pulsed)	I _{PRI_OUT_PULSE}	10ms pulse, 25% duty cycle, $I_{PRI_OUT_AVG} \le 50\%$ of rated $I_{PRI_OUT_DC}$			5.2	А	
		$V_{SEC_DC} = 12V$, $I_{PRI_OUT_DC} = 3.9A$	96.2	97			
SEC to PRI Efficiency (Ambient)	η_{AMB}	$V_{SEC_DC} = 8.1 - 12.8V$, $I_{PRL_OUT_DC} = 3.9A$	95.2			%	
		$V_{SEC_DC} = 12V$, $I_{PRI_OUT_DC} = 1.95A$	96.5	97.4			
SEC to PRI Efficiency (Hot)	η_{HOT}	$V_{SEC_DC} = 12V$, $I_{PRI_OUT_DC} = 3.9A$	96.2	97		%	
SEC to PRI Efficiency (Over Load Range)	$\eta_{20\%}$	0.78A < I _{PRI_OUT_DC} < 3.9A	90			%	
	R _{PRI_COLD}	$V_{SEC_DC} = 12V$, $I_{PRI_OUT_DC} = 3.9A$, $T_{INTERNAL} = -40$ °C	2100	2400	2700		
SEC to PRI Output Resistance	R _{PRI_AMB}	$V_{SEC_DC} = 12V$, $I_{PRI_OUT_DC} = 3.9A$	2500	2700	2900	mΩ	
	R _{PRI_HOT}	V _{SEC_DC} = 12V, I _{PRI_OUT_DC} = 3.9A, T _{INTERNAL} = 100°C	2900	3150	3400		
Primary Output Voltage Ripple	V _{PRI_OUT_PP}	$C_{PRI_OUT_EXT} = 0\mu F$, $I_{PRI_OUT_DC} = 3.9A$, $V_{SEC_DC} = 12V$, $20MHz~BW$		6250		mV	
<u> </u>	001	T _{INTERNAL} ≤ 100°C			9600		



Attribute	Symbol	Conditions / Notes	Min	Тур	Max	Unit
	Protec	tion SECONDARY to PRIMARY (Reverse Direction)				
Secondary Overvoltage Lockout Threshold	V _{SEC_OVLO+}	Module latched shut down with $V_{PRI_DC} < V_{PRI_UVLO_R}$	13.1	13.6	14.1	V
Secondary Overvoltage Lockout Response Time	t _{PRI_OVLO}			100		μs
Secondary Undervoltage Lockout Threshold	V _{SEC_UVLO} -	Module latched shut down with $V_{PRI_DC} < V_{PRI_UVLO_R}$	3.4	3.75	4.1	V
Secondary Undervoltage Lockout Response Time	t _{SEC_UVLO}			100		μs
Primary Undervoltage Lockout Threshold	V _{PRI_UVLOR}	Applies only to reversible products in forward and in reverse direction; $l_{PRI_DC} \le 20\%$ while $V_{PRI_UVLO-_R} < V_{PRI_DC} < V_{PRI_MIN}$	110	120	130	V
Primary Undervoltage Recovery Threshold	V _{PRI_UVLO+_R}	Applies only to reversible products in forward and in reverse direction	120	130	150	V
Primary Undervoltage Lockout Hysteresis	V _{PRI_UVLO_HYST_R}	Applies only to reversible products in forward and in reverse direction		10		V
Primary Output Overcurrent Trip Threshold	I _{PRI_OUT_OCP}	Module latched shut down with $V_{PRI_DC} < V_{PRI_UVLO\R}$	4.2	5.3	6.6	А
Primary Output Overcurrent Response Time Constant	t _{PRI_OUT_OCP}	Effective internal RC filter		3		ms
Primary Short Circuit Protection Trip Threshold	I _{PRI_SCP}	Module latched shut down with $V_{PRI_DC} < V_{PRI_UVLO\R}$	5.8			А
Primary Short Circuit Protection Response Time	t _{PRI_SCP}			1		μs



Operating Area

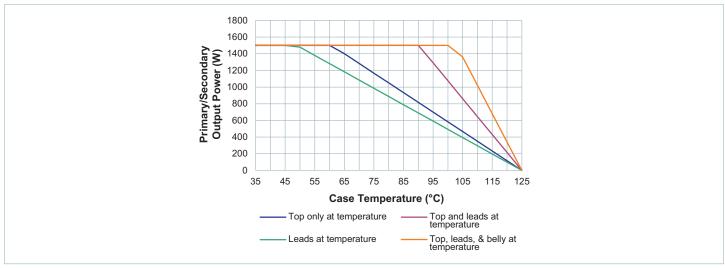


Figure 1 — Specified thermal operating area

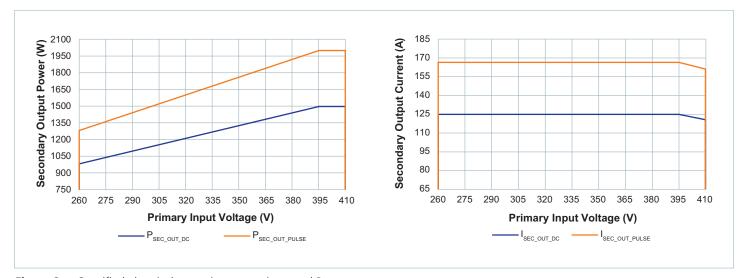


Figure 2 — Specified electrical operating area using rated $R_{SEC\ HOT}$

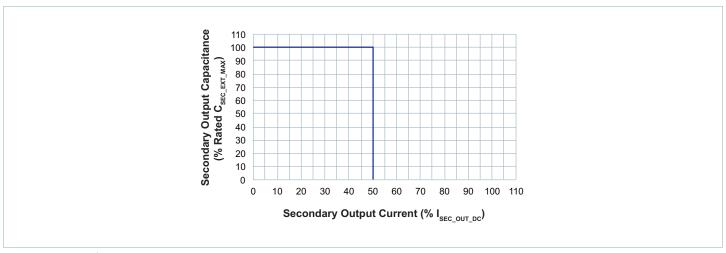


Figure 3 — Specified primary start up into load current and external capacitance



Analog Control Signal Characteristics

Specifications apply over all line and load conditions, unless otherwise noted; **boldface** specifications apply over the temperature range of $-40^{\circ}\text{C} \le T_{\text{INTERNAL}} \le 125^{\circ}\text{C}$ (T-Grade); All other specifications are at $T_{\text{INTERNAL}} = 25^{\circ}\text{C}$ unless otherwise noted.

Temperature Monitor

- \bullet The TM pin is a standard analog I/O configured as an output from an internal $\mu C.$
- The TM pin monitors the internal temperature of the controller IC within an accuracy of $\pm 5^{\circ}$ C.
- μC 250kHz PWM output internally pulled high to 3.3V.

Signal Type	State	Attribute	Symbol	Conditions / Notes	Min	Тур	Max	Unit
	Start Up	Powertrain Active to TM Time	t _{TM}			100		μs
		TM Duty Cycle	TM_PWM		18.18		68.18	%
		TM Current	I_{TM}				4	mA
		Recommended external	filtering					
		TM Capacitance (External)	C_{TM_EXT}	Recommended External filtering		0.01		μF
DIGITAL OUTPUT	Regular Operation	TM Resistance (External)	R _{TM_EXT}	Recommended External filtering		1		kΩ
		Specifications using recommended filter						
		TM Gain	A_{TM}			10		mV / °C
		TM Voltage Reference	V_{TM_AMB}	Internal temperature = 27°C		1.27		V
		TM Voltage Ripple	V _{TM PP}	$R_{TM_EXT} = 1k\Omega$, $C_{TM_EXT} = 0.01\mu$ F, $V_{PRI_DC} = 384V$, $I_{SEC_DC} = 125A$		28		mV
				T _{INTERNAL} ≤ 100°C			40	

Enable / Disable Control

- The EN pin is a standard analog I/O configured as an input to an internal μC .
- It is internally pulled high to 3.3V.
- When held low, the BCM internal bias will be disabled and the powertrain will be inactive.
- In an array of BCMs, EN pins should be interconnected to synchronize start up.

Signal Type	State	Attribute	Symbol	Conditions / Notes	Min	Тур	Max	Unit
ANALOG INPUT Regular	Start Up	EN to Powertrain Active Time	t _{EN_START}	$V_{PRI_DC} > V_{PRI_UVLO+}$, EN held low both conditions satisfied for T > $t_{PRI_UVLO+_DELAY}$		250		μs
		EN Voltage Threshold	V _{EN_TH}		2.3			V
	Regular Operation	EN Resistance (Internal)	R _{EN_INT}	Internal pull-up resistor		1.5		kΩ
	-	EN Disable Threshold	V _{EN_DISABLE_TH}				1	V



Analog Control Signal Characteristics (Cont.)

Specifications apply over all line and load conditions, unless otherwise noted; **boldface** specifications apply over the temperature range of $-40^{\circ}\text{C} \le T_{\text{INTERNAL}} \le 125^{\circ}\text{C}$ (T-Grade); All other specifications are at $T_{\text{INTERNAL}} = 25^{\circ}\text{C}$ unless otherwise noted.

Auxiliary Voltage Source

- \bullet The VAUX pin is a standard analog I/O configured as an output from an internal $\mu C.$
- VAUX is internally connected to μC output and internally pulled high to a 3.3V regulator with 2% tolerance, a 1% resistor of 1.5kΩ.
- VAUX can be used as a "Ready to process full power" flag. This pin transitions VAUX voltage after a 2ms delay from the start of powertrain activating, signaling the end of soft start.
- VAUX can be used as "Fault flag". This pin is pulled low internally when a fault protection is detected.

Signal Type	State	Attribute	Symbol	Conditions / Notes	Min	Тур	Max	Unit
	Start Up	Powertrain Active to VAUX Time	t _{VAUX}	Powertrain active to VAUX High		2		ms
ALITBLIT		VAUX Voltage	V_{VAUX}		2.8		3.3	V
		VAUX Available Current	I_{VAUX}				4	mA
		VAUX Voltage Ripple	V _{VAUX_PP}			50		mV
				T _{INTERNAL} ≤ 100°C			100	IIIV
		VAUX Capacitance (External)	C _{VAUX_EXT}				0.01	μF
		VAUX Resistance (External)	R_{VAUX_EXT}	$V_{PRI_DC} < V_{\mu C_ACTIVE}$	1.5			kΩ
	Fault	VAUX Fault Response Time	t_{VAUX_FR}	From fault to $V_{VAUX} = 2.8V$, $C_{VAUX} = 0pF$		10		μs



PMBus™ Control Signal Characteristics

Specifications apply over all line, load conditions, unless otherwise noted; **boldface** specifications apply over the temperature range of $-40^{\circ}\text{C} \leq T_{\text{INTERNAL}} \leq 125^{\circ}\text{C}$ (T-Grade); All other specifications are at $T_{\text{INTERNAL}} = 25^{\circ}\text{C}$ unless otherwise noted.

UART SER-IN / SER-OUT Pins

- Universal Asynchronous Receiver/Transmitter (UART) pins.
- The BCM communication version is not intended to be used without a Digital Supervisor.
- Isolated I²C communication and telemetry is available when using Vicor Digital Isolator and Vicor Digital Supervisor. Please see specific product data sheet for more details.
- UART SER-IN pin is internally pulled high using a 1.5k Ω to 3.3V.

Signal Type	State	Attribute	Symbol	Conditions / Notes	Min	Тур	Max	Unit
GENERAL I/O		Baud Rate	BR _{UART}	Rate		750		Kbit/s
		SER-IN Pin						
		CED IN L. L. I. V. II D	V _{SER-IN_IH}		2.3			V
		SER-IN Input Voltage Range	V _{SER-IN_IL}				1	V
DIGITAL INPUT		SER-IN Rise Time	t _{SER-IN_RISE}	10 – 90%		400		ns
1141 01		SER-IN Fall Time	t _{SER-IN_FALL}	10 – 90%		25		ns
		SER-IN R _{PULLUP}	R _{SER-IN_PLP}	Pull up to 3.3V		1.5		kΩ
	Regular Operation	SER-IN External Capacitance	C _{SER-IN_EXT}				400	pF
	Operation	SER-OUT Pin						
		SER-OUT Output Voltage Range SER-OUT Rise Time	V _{SER-OUT_OH}	$0mA \ge I_{OH} \ge -4mA$	2.8			V
			V _{SER-OUT_OL}	$0mA \le I_{OL} \le 4mA$			0.5	V
DIGITAL OUTPUT			t _{SER-OUT_RISE}	10 – 90%		55		ns
331131		SER-OUT Fall Time	t _{SER-OUT_FALL}	10 – 90%		45		ns
		SER-OUT Source Current	I _{SER-OUT}	$V_{SER-OUT} = 2.8V$			6	mA
		SER-OUT Output Impedance	Z _{SER-OUT}			120		Ω

Enable / Disable Control

- \bullet The EN pin is a standard analog I/O configured as an input to an internal $\mu C.$
- It is internally pulled high to 3.3V.
- When held low, the BCM internal bias will be disabled and the powertrain will be inactive.
- In an array of BCMs, EN pins should be interconnected to synchronize start up.
- PMBus ON/OFF command has no effect if the BCM EN pin is not in the active state. This BCM has active high EN pin logic.

Signal Type	State	Attribute	Symbol	Conditions / Notes	Min	Тур	Max	Unit
ANALOG	Start Up	EN to Powertrain Active Time	t _{EN_START}	$\begin{split} &V_{PRI_DC} > V_{PRI_UVLO+}, \\ &EN \text{ held low both conditions satisfied} \\ &for \ t > t_{PRI_UVLO+_DELAY} \end{split}$		250		μs
INPUT	Regular Operation	EN Voltage Threshold	V _{ENABLE}		2.3			V
		EN Resistance (Internal)	R _{EN_INT}	Internal pull-up resistor		1.5		kΩ
	ореганон	EN Disable Threshold	V _{EN_DISABLE_TH}				1	V



PMBus™ Reported Characteristics

Specifications apply over all line, load conditions, unless otherwise noted; **boldface** specifications apply over the temperature range of $-40^{\circ}\text{C} \leq T_{\text{INTERNAL}} \leq 125^{\circ}\text{C}$ (T-Grade); All other specifications are at $T_{\text{INTERNAL}} = 25^{\circ}\text{C}$ unless otherwise noted.

Monitored Telemetry

- The BCM communication version is not intended to be used without a Digital Supervisor.
- The current telemetry is only available in forward operation. The input and output current reported value is not supported in reverse operation.

Attribute	Digital Supervisor PMBus Read Command	Accuracy (Rated Range)	Functional Reporting Range	Update Rate	Reported Units
Input Voltage	(88h) READ_VIN	±5% (LL – HL)	130 – 450V	100µs	$V_{ACTUAL} = V_{REPORTED} \times 10^{-1}$
Input Current	(89h) READ_IIN	±20% (10 – 20% of FL) ±5% (20 – 133% of FL)	0 – 5.9A	100µs	I _{ACTUAL} = I _{REPORTED} x 10 ⁻³
Output Voltage [b]	(8Bh) READ_VOUT	±5% (LL – HL)	4.25 – 14V	100µs	$V_{ACTUAL} = V_{REPORTED} \times 10^{-1}$
Output Current	(8Ch) READ_IOUT	±20% (10 – 20% of FL) ±5% (20 – 133% of FL)	0 – 190A	100µs	$I_{ACTUAL} = I_{REPORTED} \times 10^{-2}$
Output Resistance	(D4h) READ_ROUT	±5% (50 – 100% of FL) at NL ±10% (50 – 100% of FL) (LL – HL)	1 – 3mΩ	100ms	$R_{ACTUAL} = R_{REPORTED} \times 10^{-5}$
Temperature [c]	(8Dh) READ_TEMPERATURE_1	±7°C (Full Range)	−55 to 130°C	100ms	$T_{ACTUAL} = T_{REPORTED}$

[[]c] Default READ Output Voltage returned when unit is disabled = -300V.

Variable Parameter

- Factory setting of all below Thresholds and Warning limits are 100% of listed protection values.
- Variables can be written only when module is disabled either EN pulled low or $V_{IN} < V_{IN_UVLO-}$.
- Module must remain in a disabled mode for 3ms after any changes to the below variables allowing ample time to commit changes to EEPROM.

Attribute	Digital Supervisor PMBus Command ^[d]	Conditions / Notes	Accuracy (Rated Range)	Functional Reporting Range	Default Value
Input / Output Overvoltage Protection Limit	(55h) VIN_OV_FAULT_LIMIT	V _{IN_OVLO} is automatically 3% lower than this set point	±5% (LL – HL)	130 – 435V	100%
Input / Output Overvoltage Warning Limit	(57h) VIN_OV_WARN_LIMIT		±5% (LL – HL)	130 – 435V	100%
Input / Output Undervoltage Protection Limit	(D7h) DISABLE_FAULTS	Can only be disabled to a preset default value	±5% (LL – HL)	130 – 260V	100%
Input Overcurrent Protection Limit	(5Bh) IIN_OC_FAULT_LIMIT		±20% (10 – 20% of FL) ±5% (20 – 133% of FL)	0 – 5.25A	100%
Input Overcurrent Warning Limit	(5Dh) IIN_OC_WARN_LIMIT		±20% (10 – 20% of FL) ±5% (20 – 133% of FL)	0 – 5.25A	100%
Overtemperature Protection Limit	(4Fh) OT_FAULT_LIMIT		±7°C (Full Range)	0 – 125°C	100%
Overtemperature Warning Limit	(51h) OT_WARN_LIMIT		±7°C (Full Range)	0 – 125°C	100%
Turn-On Delay	(60h) TON_DELAY	Additional time delay to the undervoltage start-up delay	±50µs	0 – 100ms	0ms

 $^{^{\}mbox{\scriptsize [e]}}$ Refer to Digital Supervisor data sheet for complete list of supported commands.

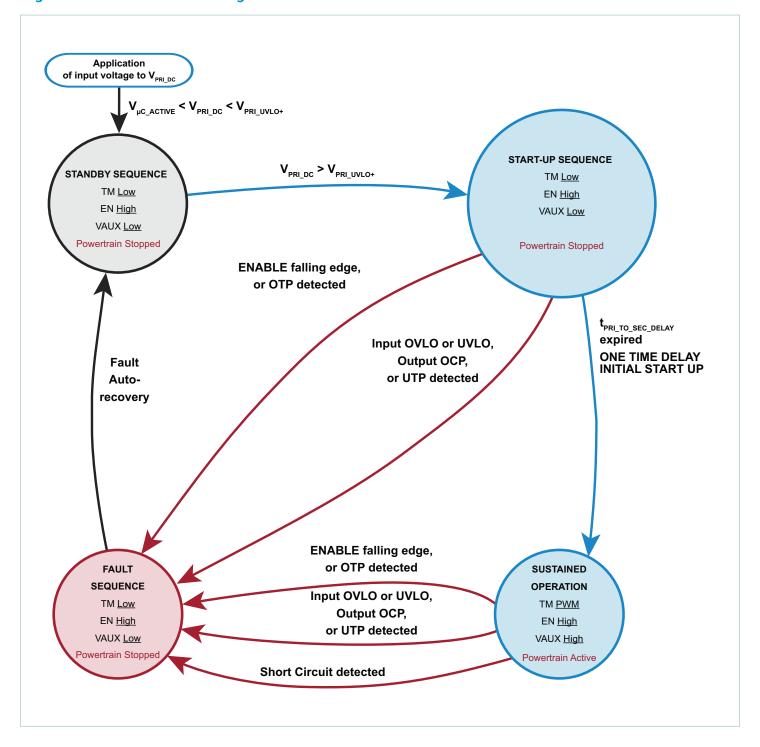


[[]d] Default READ Temperature returned when unit is disabled = -273°C.

BCM Timing Diagram



High-Level Functional State Diagram



Application Characteristics

Temperature controlled via top-side cold plate, unless otherwise noted. All data presented in this section are collected from units processing power in the forward direction (primary side to secondary side). See associated figures for general trend data.

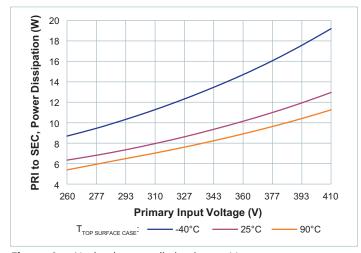


Figure 4 — No-load power dissipation vs. V_{PRI DC}

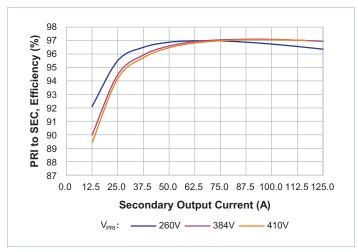


Figure 6 — Efficiency at $T_{CASE} = -40$ °C

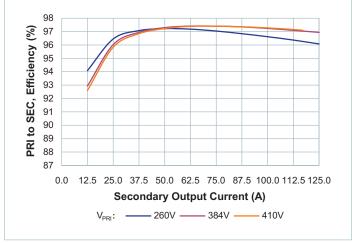


Figure 8 — Efficiency at $T_{CASE} = 25$ °C

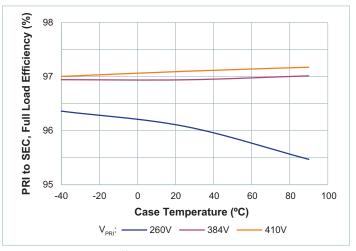


Figure 5 — Full-load efficiency vs. temperature; V_{PRI_DC}

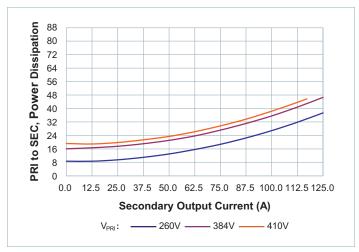


Figure 7 — Power dissipation at $T_{CASE} = -40$ °C

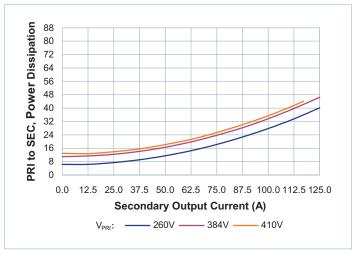


Figure 9 — Power dissipation at $T_{CASE} = 25^{\circ}C$

Application Characteristics (Cont.)

Temperature controlled via top-side cold plate, unless otherwise noted. All data presented in this section are collected from units processing power in the forward direction (primary side to secondary side). See associated figures for general trend data.

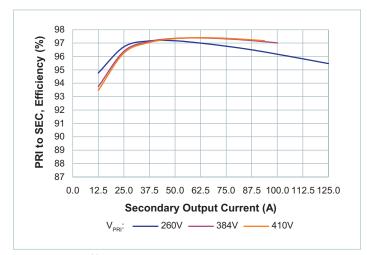


Figure 10 — Efficiency at $T_{CASE} = 90$ °C

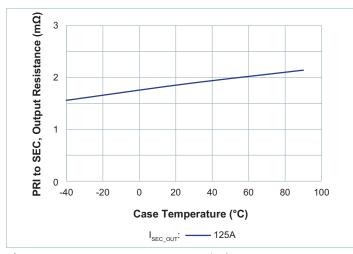


Figure 12 — R_{SEC} vs. temperature; nominal V_{PRI_DC} $I_{SEC_DC} = 100A$ at $T_{CASE} = 90^{\circ}C$

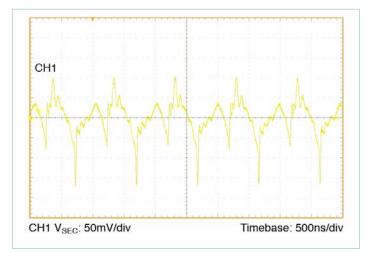


Figure 14 — Full-load secondary voltage, $10\mu F C_{PRI_IN_EXT}$; no external $C_{SEC_OUT_EXT}$. Board-mounted module, scope setting: 20MHz analog BW

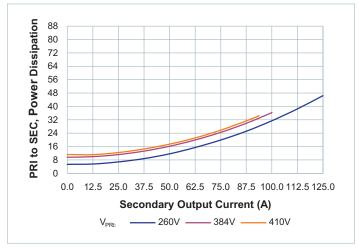


Figure 11 — Power dissipation at $T_{CASE} = 90$ °C

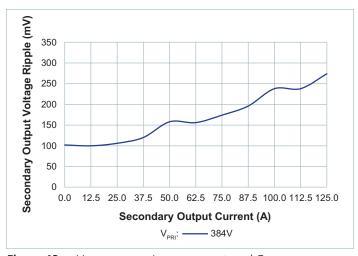


Figure 13 — $V_{SEC_OUT_PP}$ vs. I_{SEC_DC} ; no external $C_{SEC_OUT_EXT.}$ Board-mounted module, scope setting: 20MHz analog BW

Application Characteristics (Cont.)

Temperature controlled via top-side cold plate, unless otherwise noted. All data presented in this section are collected from units processing power in the forward direction (primary side to secondary side). See associated figures for general trend data.

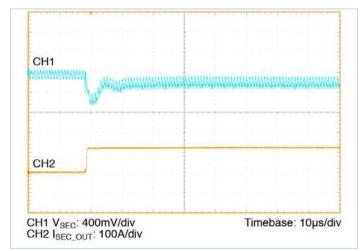


Figure 15 — 0 – 125A transient response: $C_{PRI\ IN\ EXT} = 10\mu F$, no external $C_{SEC\ OUT\ EXT}$

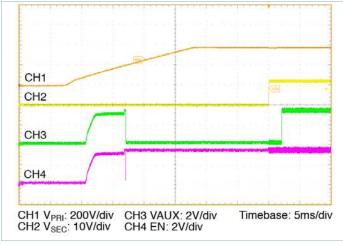


Figure 17 — Start up from application of $V_{PRI_DC} = 384V$, 50% $I_{SEC\ OUT\ DG}$, 100% $C_{SEC\ OUT\ EXT}$

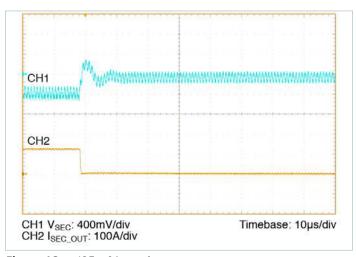


Figure 16 — 125 – 0A transient response: $C_{PRI_IN_EXT} = 10\mu F$, no external $C_{SEC_OUT_EXT}$

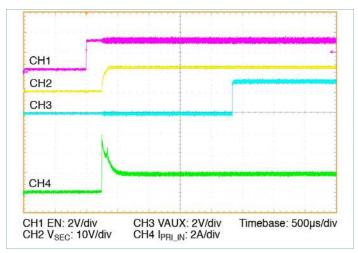


Figure 18 — Start up from application of EN with pre-applied $V_{PRI_DC} = 384V$, 50% $I_{SEC_OUT_DG}$, 100% $C_{SEC_OUT_EXT}$

General Characteristics

Attribute Symbol		Conditions / Notes	Min	Тур	Max	Unit			
		Mechanical							
Length	L		60.87 [2.396]	61.00 [2.402]	61.13 [2.407]	mm [in]			
Width	W		24.76 [0.975]	25.14 [0.990]	25.52 [1.005]	mm [in]			
Height	Н		7.11 [0.280]	7.21 [0.284]	7.31 [0.288]	mm [in]			
Volume	Vol	Without heatsink		11.06 [0.675]		cm³ [in³]			
Weight	W			41 [1.45]		g [oz]			
		Nickel	0.51		2.03				
Lead Finish		Palladium	0.02		0.15	μm			
		Gold	0.003		0.051				
		Thermal							
Operating Temperature	T _{INTERNAL}	BCM6123xD1E13A3yzz (T-Grade)	-40		125	°C			
Operating lemperature		BCM6123xD1E13A3yzz (M-Grade)	-55		125	°C			
Thermal Resistance Top Side	$\theta_{INT-TOP}$	Estimated thermal resistance to maximum temperature internal component from isothermal top		1.1		°C/W			
Thermal Resistance Leads	$\theta_{ ext{INT-LEADS}}$	Estimated thermal resistance to maximum temperature internal component from isothermal leads		1.4		°C/W			
Thermal Resistance Bottom Side	$\theta_{INT-BOTTOM}$	Estimated thermal resistance to maximum temperature internal component from isothermal bottom		1.1		°C/W			
Thermal Capacity				34		Ws/°C			
		Assembly							
Storage Temperature		BCM6123xD1E13A3yzz (T-Grade)	- 55		125	°C			
Storage remperature		BCM6123xD1E13A3yzz (M-Grade)	-65		125	°C			
ESD Withstand	ESD _{HBM}	Human Body Model, "ESDA / JEDEC JDS-001-2012" Class I-C (1kV to < 2kV)							
LOD MINISTALIA	ESD _{CDM}	Charge Device Model, "JESD 22-C101-E" Class II (200V to < 500V)							



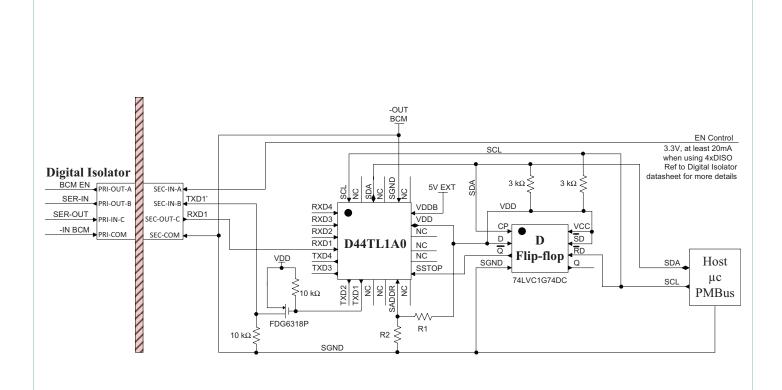
General Characteristics (Cont.)

Attribute	Symbol	Conditions / Notes	Min	Тур	Max	Unit			
Soldering ^[e]									
Peak Temperature Top Case					135	°C			
		Safety							
		PRIMARY to SECONDARY	4,242						
Isolation voltage / Dielectric test	V_{HIPOT}	PRIMARY to CASE	2,121			V_{DC}			
		SECONDARY to CASE	2,121						
Isolation Capacitance	C _{PRI_SEC}	Unpowered Unit	620	780	940	pF			
Insulation Resistance	R _{PRI_SEC}	At 500V _{DC}	10			MΩ			
MTBF		MIL-HDBK-217Plus Parts Count - 25°C Ground Benign, Stationary, Indoors / Computer		2.31		MHrs			
		Telcordia Issue 2 - Method I Case III; 25°C Ground Benign, Controlled		3.41		MHrs			
		cTÜVus EN 60950-1							
Agency Approvals / Standards		cURus UL 60950-1							
		CE Marked for Low Voltage Directive and RoHS Recast Directive, as applicable							
		Previous Part Numbers							
BCM384x120y1K5ACz									
BCM384x120y1K5AC1									

^[f] Product is not intended for reflow solder attach.



PMBus™ System Diagram



The PMBus communication enabled bus converter provides accurate telemetry monitoring and reporting, threshold and warning limits adjustment, in addition to corresponding status flags.

The BCM internal μ C is referenced to primary ground. The Digital Isolator allows UART communication interface with the host Digital Supervisor at typical speed of 750kHz across the isolation barrier. One of the advantages of the Digital Isolator is its low power consumption. Each transmission channel is able to draw its internal bias circuitry directly from the input signal being transmitted to the output with minimal to no signal distortion.

The Digital Supervisor provides the host system μ C with access to an array of up to four BCMs. This array is constantly polled for status by the Digital Supervisor. Direct communication to individual BCM is enabled by a page command. For example, the page (0x00) prior to a telemetry inquiry points to the Digital Supervisor data and pages (0x01 – 0x04) prior to a telemetry inquiry points to the array of BCMs connected data. The Digital Supervisor constantly polls the BCM data through the UART interface.

The Digital Supervisor enables the PMBus compatible host interface with an operating bus speed of up to 400kHz. The Digital Supervisor follows the PMBus command structure and specification.

Please refer to the Digital Supervisor data sheet for more details.



BCM in a ChiP™

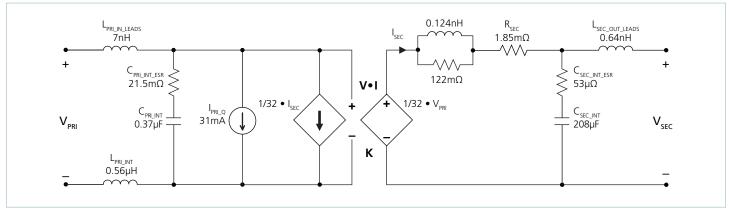


Figure 19 — BCM AC model

The BCM uses a high-frequency resonant tank to move energy from primary to secondary and vice versa. The resonant LC tank, operated at high frequency, is amplitude modulated as a function of the primary voltage and the secondary current. A small amount of capacitance embedded in the primary and secondary stages of the module is sufficient for full functionality and is key to achieving high power density.

The BCM6123xD1E13A3yzz can be simplified into the model shown in Figure 19.

At no load:

$$V_{SEC} = V_{PRI} \bullet K \tag{1}$$

K represents the "turns ratio" of the BCM. Rearranging Equation 1:

$$K = \frac{V_{SEC}}{V_{PRI}} \tag{2}$$

In the presence of a load, V_{SEC} is represented by:

$$V_{SEC} = V_{PRI} \bullet K - I_{SEC} \bullet R_{SEC}$$
 (3)

and I_{SEC} is represented by:

$$I_{SEC} = \frac{I_{PRI} - I_{PRI_Q}}{K} \tag{4}$$

 R_{SEC} represents the impedance of the BCM, and is a function of the R_{DS_ON} of the primary and secondary MOSFETs and the winding resistance of the power transformer. I_{PRI_Q} represents the quiescent current of the BCM controller, gate drive circuitry and core losses.

The effective DC voltage transformer action provides additional interesting attributes. Assuming that $R_{SEC} = 0\Omega$ and $I_{PRI_Q} = 0A$, Equation 3 now becomes Equation 1 and is essentially load independent, resistor R is now placed in series with V_{PRI} .

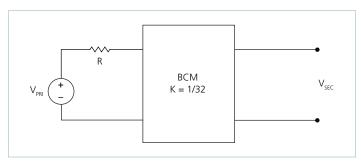


Figure 20 — K = 1/32 BCM with series primary resistor

The relationship between V_{PRI} and V_{SEC} becomes:

$$V_{SFC} = (V_{PRI} - I_{PRI} \bullet R) \bullet K \tag{5}$$

Substituting the simplified version of Equation 4 (I_{PRI_O} is assumed = 0A) into Equation 5 yields:

$$V_{SEC} = V_{PRI} \bullet K - I_{SEC} \bullet R \bullet K^2 \tag{6}$$

This is similar in form to Equation 3, where R_{SEC} is used to represent the characteristic impedance of the BCM. However, in this case a real resistor, R on the primary side of the BCM is effectively scaled by K^2 with respect to the secondary.

Assuming that $R = 1\Omega$, the effective R as seen from the secondary side is $1m\Omega$, with K = 1/32.

A similar exercise can be performed with the addition of a capacitor or shunt impedance at the primary of the BCM. A switch in series with V_{PRI} is added to the circuit. This is depicted in Figure 21.

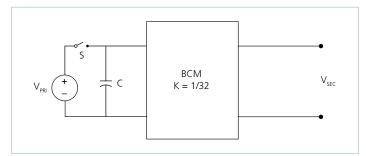


Figure 21 — BCM with primary capacitor

A change in V_{PRI} with the switch closed would result in a change in capacitor current according to the following equation:

$$I_{C}(t) = C \frac{dV_{PRI}}{dt} \tag{7}$$

Assume that with the capacitor charged to V_{PRI} , the switch is opened and the capacitor is discharged through the idealized BCM. In this case,

$$I_C = I_{SEC} \bullet K \tag{8}$$

substituting Equation 1 and 8 into Equation 7 reveals:

$$I_{SEC}(t) = \frac{C}{K^2} \bullet \frac{dV_{SEC}}{dt} \tag{9}$$

The equation in terms of the secondary has yielded a K^2 scaling factor for C, specified in the denominator of the equation.

A K factor less than unity results in an effectively larger capacitance on the secondary when expressed in terms of the primary. With K = 1/32 as shown in Figure 21, $C = 1\mu F$ would appear as $C = 1024\mu F$ when viewed from the secondary.

Low impedance is a key requirement for powering a high-current, low-voltage load efficiently. A switching regulation stage should have minimal impedance while simultaneously providing appropriate filtering for any switched current. The use of a BCM between the regulation stage and the point of load provides a dual benefit of scaling down series impedance leading back to the source and scaling up shunt capacitance or energy storage as a function of its K factor squared. However, these benefits are not achieved if the series impedance of the BCM is too high. The impedance of the BCM must be low, i.e., well beyond the crossover frequency of the system.

A solution for keeping the impedance of the BCM low involves switching at a high frequency. This enables the use of small magnetic components because magnetizing currents remain low. Small magnetics mean small path lengths for turns. Use of low-loss core material at high frequencies also reduces core losses.

The two main terms of power loss in the BCM are:

- No load power dissipation (P_{PRI_NL}): defined as the power used to power up the module with an enabled powertrain at no load.
- Resistive loss (P_{RSEC}): refers to the power loss across the BCM modeled as pure resistive impedance.

$$P_{DISSIPATED} = P_{PRI_NL} + P_{R_{SFC}} \tag{10}$$

Therefore,

$$P_{SEC_OUT} = P_{PRI_IN} - P_{DISSIPATED} = P_{PRI_IN} - P_{PRI_NL} - P_{RSEC}$$
 (11)

The above relations can be combined to calculate the overall module efficiency:

$$\eta = \frac{P_{SEC_OUT}}{P_{PRI_IN}} = \frac{P_{PRI_IN} - P_{PRI_NL} - P_{RSEC}}{P_{PRI_IN}}$$
(12)

$$= \frac{V_{\scriptscriptstyle PRI} \bullet I_{\scriptscriptstyle PRI} - P_{\scriptscriptstyle PRI_NL} - (I_{\scriptscriptstyle SEC})^2 \bullet R_{\scriptscriptstyle SEC}}{V_{\scriptscriptstyle PRI} \bullet I_{\scriptscriptstyle PRI}}$$

$$=1-\left(\frac{P_{\mathit{PRI_NL}}+(I_{\mathit{SEC}})^2\bullet R_{\mathit{SEC}}}{V_{\mathit{PRI}}\bullet I_{\mathit{PRI}}}\right)$$

